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the dielectric material including an oxide disposed above said nitride liner such that said oxide extends above the uppermost surface of said nitride liner to substantially a top surface of said substrate, such that substantially no polysilicon material is disposed within the trench.

In claim 7, line 1, change "6" to -- 1 --.

8. (Twice Amended) A shallow trench isolation in a substrate, said shallow trench isolation structure comprising:

a trench in the substrate;

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a nitride liner recessed within said trench such that an uppermost surface of said nitride liner is below a channel depth, said channel depth being representative of a depth of a channel associated with a device disposed beside said trench; [and]

an oxide fill disposed above said nitride liner, such that said oxide fill extends above and below [an] the uppermost surface of said nitride liner substantially to a top surface of said substrate and completely filling below the uppermost surface, respectively[.]; and

the oxide fill is disposed above said liner such that substantially no polysilicon material is disposed within the trench.

In claim 10, line 1, change "9" to -- 8 --.

Please add the following new claims:

Sub B-3
24. (New) A shallow trench isolation structure for preventing hot carrier effects due to charge trapping, said shallow trench isolation structure comprising:

a trench in the substrate;

an oxide liner formed lining the trench and a top surface of the substrate;